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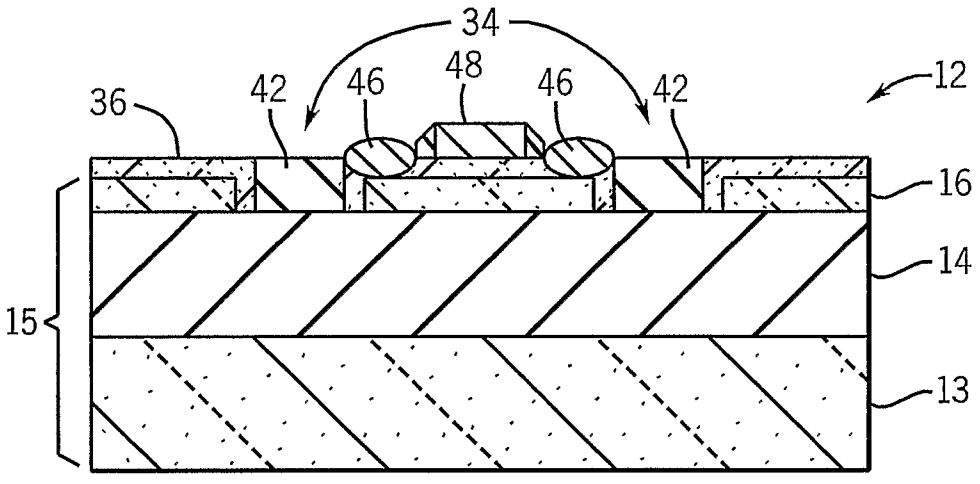
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(54) Title: SHALLOW TRENCH ISOLATION PROCESS AND STRUCTURE



(57) Abstract: A method of manufacturing an integrated circuit (IC) utilizes a shallow trench isolation (STI) technique. The shallow trench isolation technique is used in strained silicon (SMOS) process. The strained material (36) is formed after the trench (34) is formed. The process can be utilized on a compound semiconductor layer (15) above a buried oxide (Box) layer (14).

WO 2005/071738 A2